

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5260QA.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
I _C	collector current			-	-	2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	3	А
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_C = 1 \text{ A}; \ I_B = 0.1 \text{ A}; \ \text{pulsed}; \ t_p \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02 \ ; \ T_{\text{amb}} = 25 \ ^\circ\text{C} \end{split}$		-	130	180	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	E	emitter		в
3	С	collector	4 3	- N
4	С	collector		E sym123
			Transparent top view DFN1010D-3 (SOT1215)	

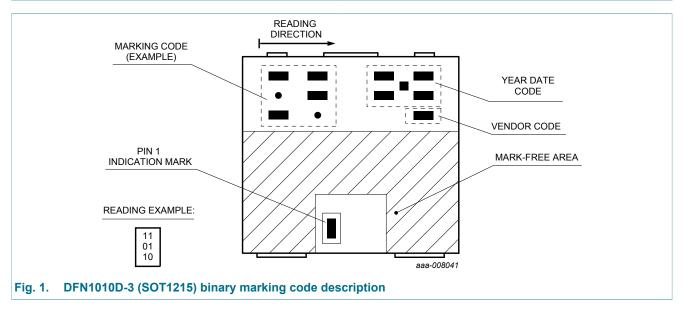
6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS4260QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4260QA	11 11 00



PBSS4260QA

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8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А
I _B	base current			-	0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

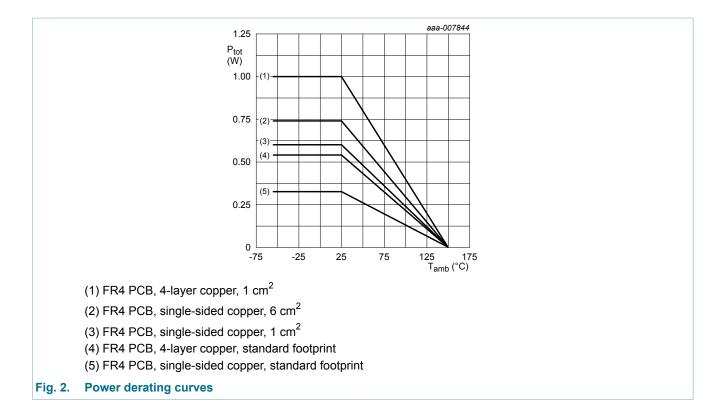
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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9. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-a)} thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W		
		[2]	-	-	209	K/W		
	ampient		[3]	-	-	169	K/W	
			[4]	-	-	232	K/W	
			[5]	-	-	125	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

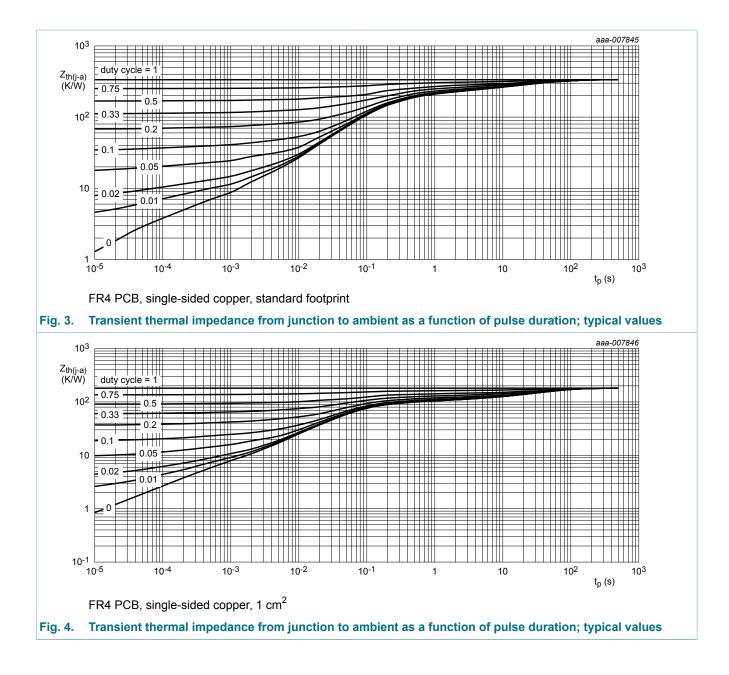
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

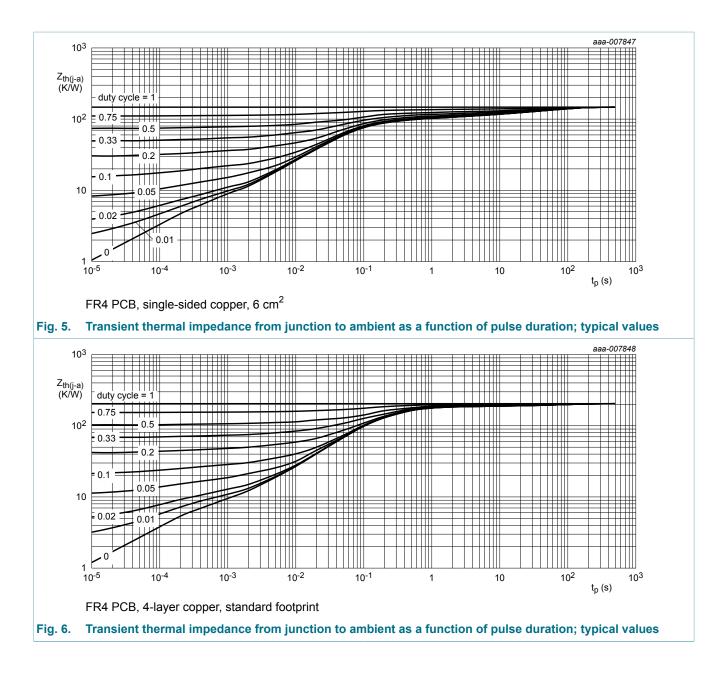


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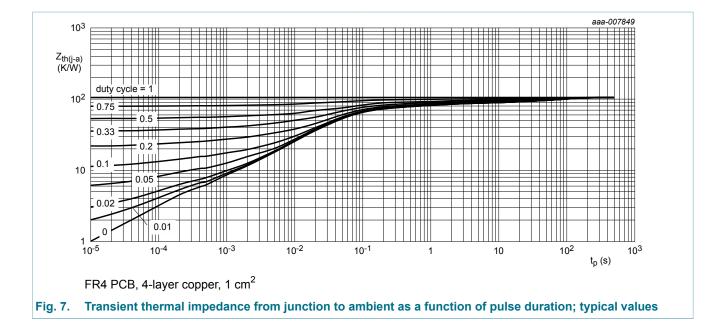


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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE} DC current gain	DC current gain	V_{CE} = 2 V; I _C = 100 mA; pulsed; t _p ≤ 300 µs; \overline{o} ≤ 0.02 ; T _{amb} = 25 °C	235	400	-	
		$\begin{split} V_{CE} &= 2 \text{ V; } I_C = 500 \text{ mA; pulsed;} \\ t_p &\leq 300 \mu\text{s; } \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{split}$	150	240	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; V; \; I_C = 1 \; A; \; \text{pulsed}; \; t_p \leq 300 \; \mu s; \\ \delta &\leq 0.02 \; ; \; T_{amb} = 25 \; ^\circ \text{C} \end{split}$	85	125	-	
		$V_{CE} = 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	40	65	-	
OL3di -	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	75	100	mV
		I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	145	190	mV
		I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\bar{o} \le 0.02$; T_{amb} = 25 °C	-	130	180	mV

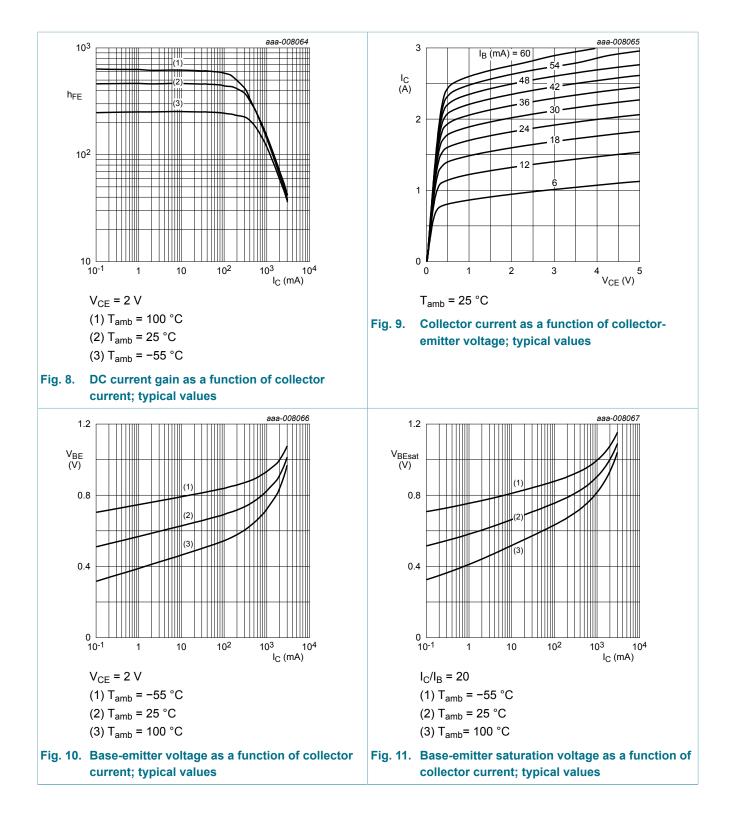
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	275	370	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	250	350	mV
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_{C} &= 1 \text{ A}; I_{B} = 0.1 \text{ A}; \text{ pulsed}; t_{p} \leq 300 \mu\text{s}; \\ \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	130	180	mΩ
V _{BEsat} base-emitter saturation voltage	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.88	1	V
	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.91	1.05	V	
		I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	1	1.15	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	1.05	1.2	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:VcE} \begin{array}{l} V_{CE} = 2 \; V; \; I_{C} = 0.5 \; A; \; pulsed; \\ t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}C \end{array}$	-	0.77	0.9	V
t _d	delay time	V_{CC} = 10 V; I _C = 0.5 A; I _{Bon} = 25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = -25 mA; T _{amb} = 25 °C	-	85	-	ns
t _{on}	turn-on time		-	100	-	ns
t _s	storage time		-	545	-	ns
t _f	fall time		-	125	-	ns
t _{off}	turn-off time		-	670	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C	120	180	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	4.7	6	pF

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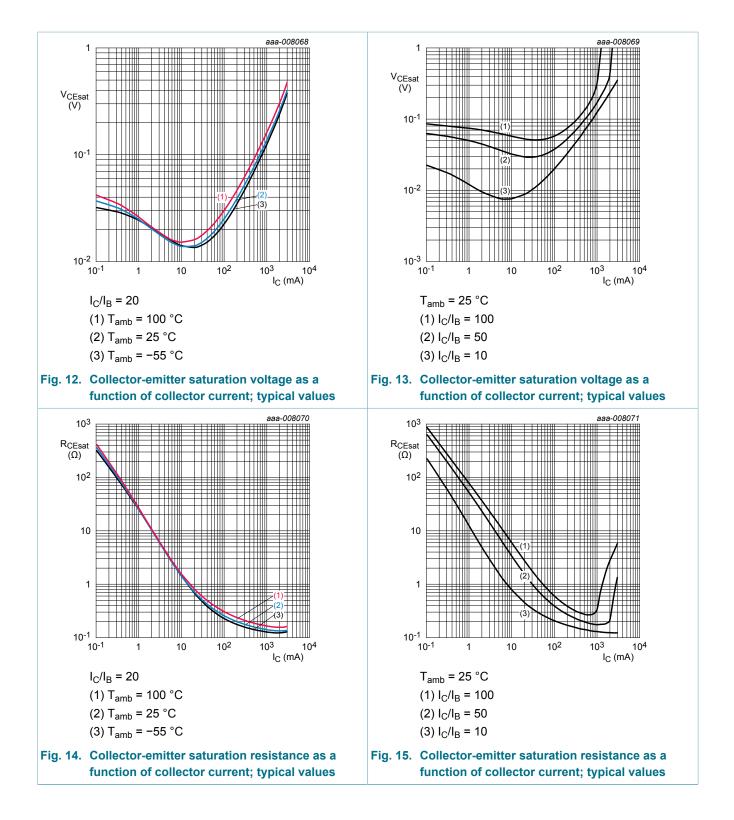


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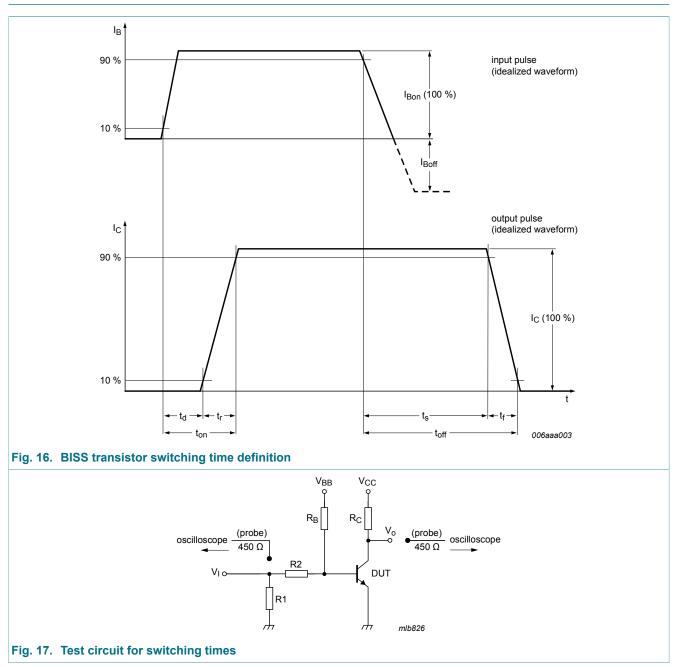


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11. Test information

11.1 Quality information

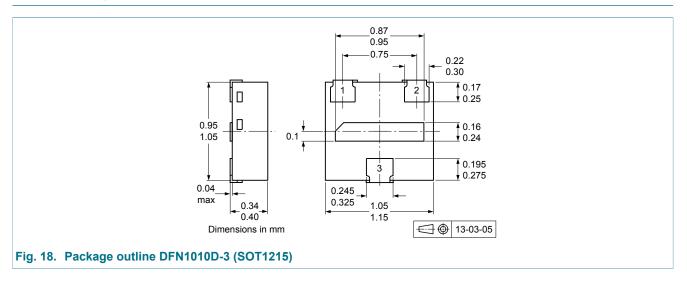
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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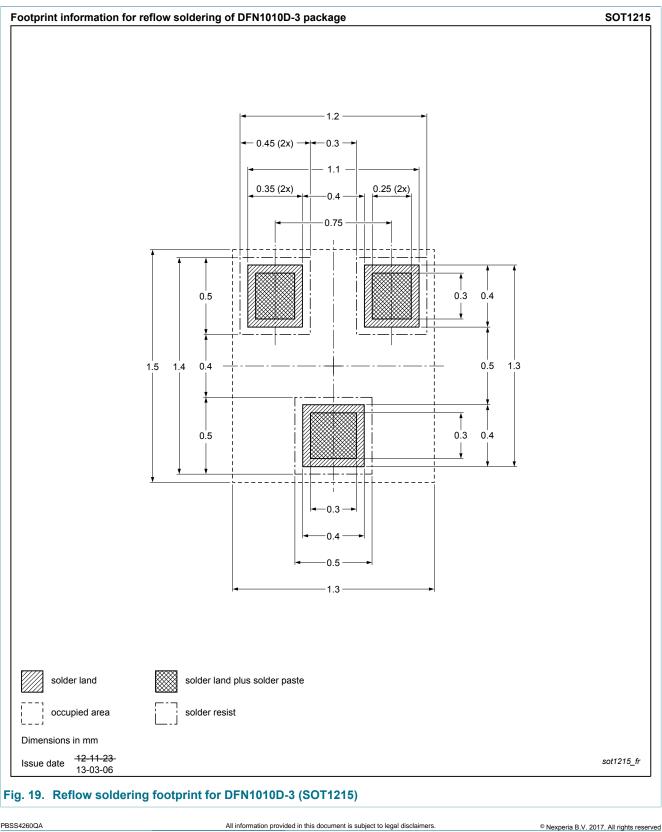
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4260QA v.1	20130828	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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